## B.Sc. ELECTRONICS SYLLABUS B.Sc. I YEAR Semester - II DSC- Paper –II : Electronic Devices

## UNIT-I

Total number of hours : 56 No of hours per week: 4 Credits :4

**PN** Junction: Formation of PN junction, Depletion region, Junction capacitance, Diode equation (no derivation) Effect of temperature on reverse saturation current , V -I characteristics and simple applications of i) Junction diode, ii) Zener diode, iii) Tunnel diode and iv) Varactor diode.

## UNIT-II

Bipolar Junction Transistor( BJT) : PNP and NPN transistors, current components in BJT, BJT static characteristics (Input and Output), Early effect, CB, CC, CE configurations of transistor and bias conditions ( cut off, active, and saturation regions ), CE configuration as two port network, h – parameter model and its equivalent circuit. Determination of h - parameters from the characteristics. Load line analysis ( AC and DC ). Transistor Biasing - Fixed and self bias.

## UNIT- III

Field Effect Transistor (FET): Construction and working of JFET, output and transfer characteristics of FET, Determination of FET parameters. Application of FET as Voltage variable resistor. Advantages of FET over BJT. MOSFET :: construction and working of enhancement and depletion modes, output and transfer characteristics Application of MOSFET as a switch.

Uni Junction Transistor (UJT): Construction and working of UJT and its Characteristics. Application of UJT as a relaxation oscillator.

## UNIT- IV

Silicon Controlled Rectifier (SCR): Construction and working of SCR. Two transistor representation, Characteristics of SCR. Application of SCR for power control.

Photo electronic Devices: Construction and Characteristics of Light Dependent Resistor (LDR), Photo voltaic Cell, Photo diode, Photo transistor and Light Emitting

# **Books Recommended:**

- 1) Electronic Devices and circuits-Millman and Halkias,(TMH)
- 2) Principles of Electronics-V K.Mehta & Rohit Mehta
- 3) Electronic Devices and Ciacuits-Allen Moltershed(PHI)
- 4) Basic Electronics and Linear Circuits-Bhar, hava U
- 5) Electronic Devices and Coults-Y.N.Bapat 6) Electronic Devices and Circuits-Mithal.
- 7) Experiments in Electronics-S.V.Subramanyam.

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## B.Sc. I Year, Semester – II : Electronics Practical Paper – II : Electronic Devices Lab

#### No. of hours per week: 3

- 1. To draw volt- ampere characteristics of Junction diode and determine the cut in voltage, forward and reverse resistances.
- 2. Zener diode V I Characteristics Determination of Zener breakdown voltage.
- 3. Voltage regulator ( line and load ) using Zener diode.
- **4.** BJT input and output characteristics (CE configuration) and determination of 'h' parameters.
- 5. FET Characteristics and determination of FET parameters.
- 6. UJT characteristics determination of intrinsic standoff ratio.
- 7. UJT as relaxation oscillator.
- 8 Characteristics of LDR/Photo diode/Photo transistor/Solar cell.

# Note: Student has to perform minimum of Six experiments.

### Reference Books:

1) Lab manual for Electronic Devices and Circuits – 4<sup>th</sup> Edition. By David A Bell - PHI

Normer.

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